

Abstract

[Proposed is a] A semiconductor arrangement and a method for manufacturing the semiconductor arrangement are provided,
5 which arrangement and method allow an improvement in the current-carrying capacity for given chip dimensions. The semiconductor arrangement includes trenches [10] introduced in the interior of the chip, [in order to] which trenches reduce power loss and improve the heat dissipation of the chip, as
10 well as reduce the forward voltage of the diode.

[(Figure 1a)]